

深圳市晶泰源电子有限公司

KTA1270 TRANSISTOR (PNP)

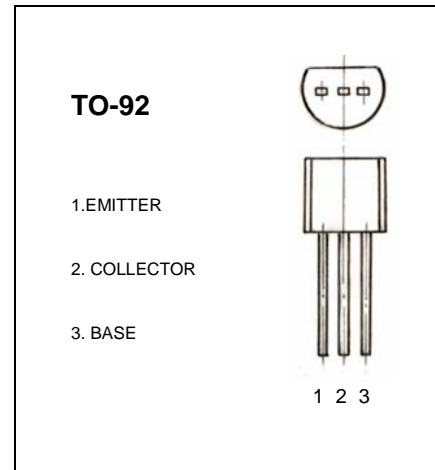
FEATURES

GENERAL PURPOSE APPLICATION SWITCHING

APPLICATION

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	-35	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –Continuous	-0.5	A
P_C	Collector Power Dissipation	500	mW
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	h_{FE1}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		240	
	h_{FE2}	$V_{CE} = -6\text{V}, I_C = -400\text{mA}$	25			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.25	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$ $f = 100\text{MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF

CLASSIFICATION OF h_{FE}

Rank		O	Y
Range	$h_{FE(1)}$	70-140	120-240
	$h_{FE(2)}$	25(min)	40(min)